

Total No. of Questions : 09]

SEAT No. :

P-9067

[Total No. of Pages : 4

[6178] - 2

F.E.

ENGINEERING PHYSICS

(2019 Pattern) (Semester - I/II) (107002)

Time : 2½ Hours]

[Max. Marks : 70

Instructions to the candidates :

- 1) Q. 01 is compulsory, Answer Q2 or Q3, Q4 or Q5, Q6 or Q7, Q8 or Q9.
- 2) Neat diagrams must be drawn wherever necessary.
- 3) Figures to the right indicates full marks.
- 4) Use of Electronic pocket calculator is allowed.
- 5) Assume suitable data, if necessary.

Physical Constants : -

- Plank's constant $h = 6.63 \times 10^{-34}$ J.S
- Mass of electron $m_e = 9.1 \times 10^{-31}$ Kg
- Charge on election $e = 1.6 \times 10^{-19}$ C

Q1) Write the correct option with answer for the following (1 mark each). [10]

- i) The de Broglie wavelength is _____ proportional to mass of the particle and _____ proportional to velocity of the particle
 - a) Directly, directly
 - b) Inversely, inversely,
 - c) Directly, inversely
 - d) Inversely, directly
- ii) If a wave function is finite, single valued, continuous and normalizable it is called as
 - a) Well behaved function
 - b) Probability function,
 - c) Fermi function
 - d) None of these
- iii) Heisenberg Uncertainty Principle is the product of _____ in position and momentum
 - a) Difference
 - b) Uncertainties
 - c) Addition
 - d) Subtraction

P.T.O.

- Q3)** a) Derive the equation for energy of the particle is enclosed in a one-dimensional rigid box (infinite potential well). [6]
b) State de Broglie hypothesis. Derive the equation of de Broglie wavelength for an electron accelerated by a potential difference “V”. [5]
c) An electron has a speed of 600 m/s with an accuracy of 0.005 %. Find the uncertainty in its 4 position. [4]

- Q4)** a) Explain classification of solids on the basis of Band Theory. [6]
b) Explain the working of PN junction diode in (a) forward bias (c) reverse bias on the basis of energy level diagram. [5]
c) Calculate the mobility of charge carriers in doped silicon whose conductivity is 100 per Ω -m and the Hall coefficient is $3.6 \times 10^{-4} \text{ m}^3/\text{coulomb}$. [4]

OR

- Q5)** a) Explain Hall effect. Derive the equation of Hall coefficient. [6]
b) Prove that in intrinsic semiconductor fermi level lies exactly at centre between valence band and conduction band. [5]
c) Calculate the conductivity of pure silicon at room temperature when concentration of carriers is 1.6×10^{10} per cc [$\mu_e=1500 \text{ cm}^2/\text{V-sec}$, $\mu_n=500 \text{ cm}^2/\text{V-sec}$]. [4]

- Q6)** a) Differentiate between type I and type II superconductors. [6]
b) Define the terms: [5]
i) Magnetic field strength (H)
ii) Magnetization (M)
iii) Magnetic Susceptibility (χ)
iv) Magnetic Induction (B)
v) Relative Permeability (μ)
c) Explain DC and AC Josephson effect in brief. [4]

OR

- Q7)** a) Explain how the information is recorded and retrieved in magneto-optical recording devices. [6]
b) State and Explain Meissner effect. Show that superconductors exhibit perfect diamagnetism. [5]
c) Differentiate ferromagnetic materials and paramagnetic material. (Any two points) [4]

- Q8)** a) Explain Electrical and Mechanical properties of nanoparticles. [6]
b) Differentiate between Non-Destructive Testing techniques and destructive testing techniques. [5]
c) Explain the applications of Nano particles in Targeted Drug Delivery. [4]

OR

- Q9)** a) What is Non Destructive Testing? Explain Ultrasonic Testing Technique for flaw detection. [6]
b) Explain nano technology is used in, Automobile and electronics field.[5]
c) An ultrasonic pulse of frequency 130 kHz is sent through a block of steel. The echo pulse is recorded after 1.695 microseconds. If the velocity of ultrasonic in steel is 5900 m/s, calculate the thickness of the steel block and the wavelength of the pulse. [4]

